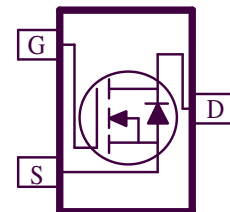
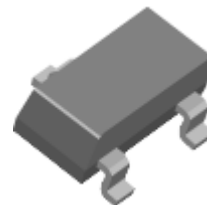


N-Channel 30-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

- Low $r_{DS(on)}$ provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe SOT-23 saves board space
- Fast switching speed
- High performance trench technology

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ m(Ω)	I_D (A)
30	32 @ $V_{GS} = 10V$	5.2
	64 @ $V_{GS} = 4.5V$	3.7



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ C$ UNLESS OTHERWISE NOTED)			
Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ^a	$T_A = 25^\circ C$	I_D	A
	$T_A = 70^\circ C$		
Pulsed Drain Current ^b	I_{DM}	30	
Continuous Source Current (Diode Conduction) ^a	I_S	1.6	A
Power Dissipation ^a	$T_A = 25^\circ C$	P_D	W
	$T_A = 70^\circ C$		
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ C$

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Maximum	Units
Maximum Junction-to-Ambient ^a	$t \leq 5$ sec	100	$^\circ C/W$
	Steady-State	166	$^\circ C/W$

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Parameter	Symbol	Test Conditions	Limits			Unit
			Min	Typ	Max	
Static						
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1		3	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 V, V_{GS} = 20 V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 24 V, V_{GS} = 0 V$			1	uA
		$V_{DS} = 24 V, V_{GS} = 0 V, T_J = 55^\circ C$			25	
On-State Drain Current ^A	$I_{D(on)}$	$V_{DS} = 5 V, V_{GS} = 10 V$	20			A
Drain-Source On-Resistance ^A	$r_{DS(on)}$	$V_{GS} = 10 V, I_D = 5.2 A$			32	m Ω
		$V_{GS} = 4.5 V, I_D = 3.7 A$			64	
Forward Transconductance ^A	g_{fs}	$V_{DS} = 15 V, I_D = 5.2 A$		40		S
Diode Forward Voltage	V_{SD}	$I_S = 2.3 A, V_{GS} = 0 V$		0.7		V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 15 V, V_{GS} = 4.5 V,$ $I_D = 5.2 A$		4.0		nC
Gate-Source Charge	Q_{gs}			1.1		
Gate-Drain Charge	Q_{gd}			1.4		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 25 V, R_L = 25 \Omega, I_D = 1 A,$ $V_{GEN} = 10 V$		16		nS
Rise Time	t_r			5		
Turn-Off Delay Time	$t_{d(off)}$			23		
Fall-Time	t_f			3		

Notes

- Pulse test: $PW \leq 300 \mu s$ duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.

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Typical Electrical Characteristics (N-Channel)

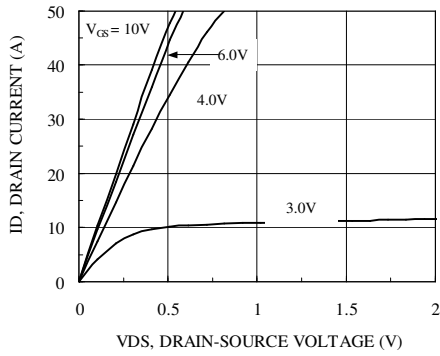


Figure 1. On-Region Characteristics

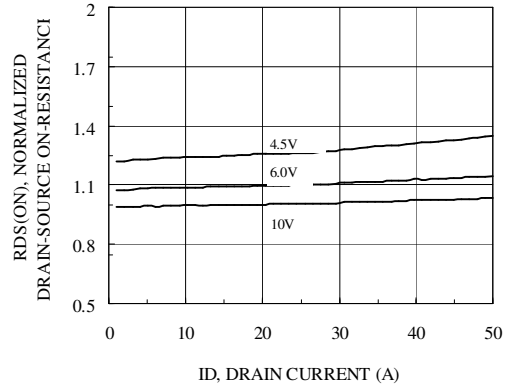


Figure 2. On-Resistance with Drain Current

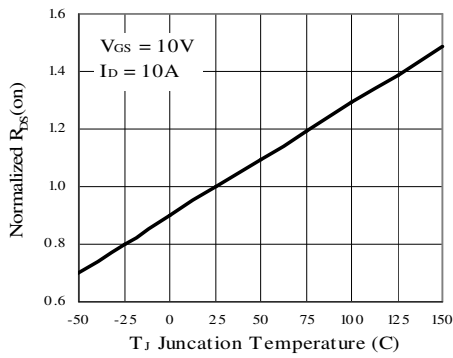


Figure 3. On-Resistance Variation with Temperature

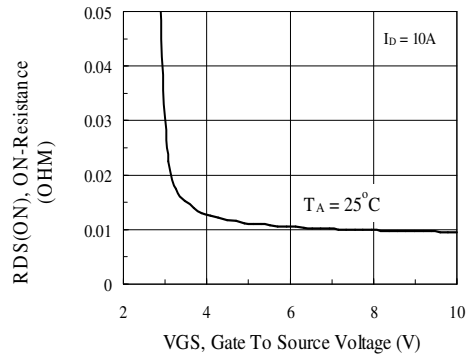


Figure 4. On-Resistance Variation with Gate to Source Voltage

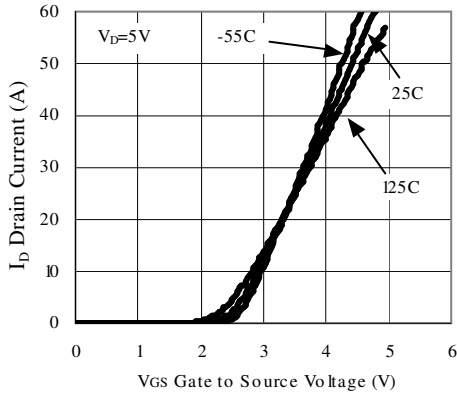


Figure 5. Transfer Characteristics

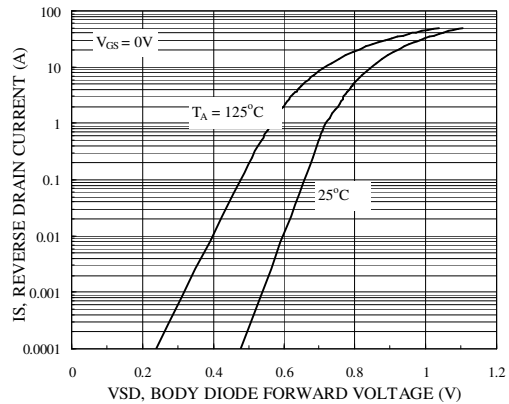


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

Typical Electrical Characteristics (N-Channel)

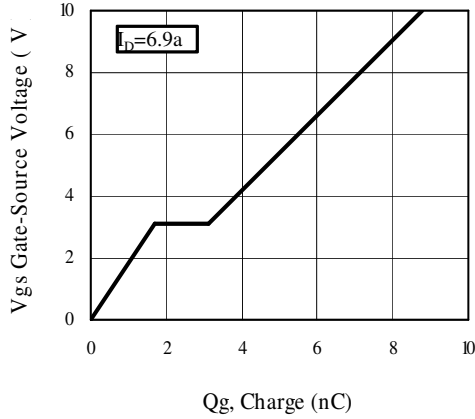


Figure 7. Gate Charge Characteristics

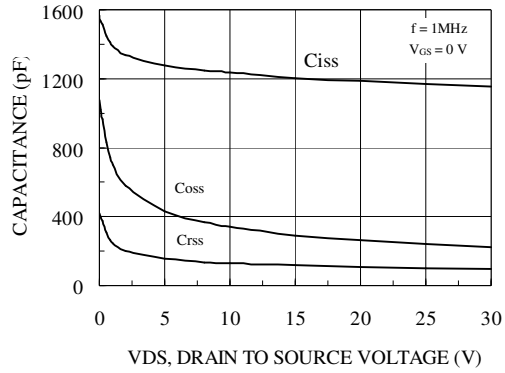


Figure 8. Capacitance Characteristics

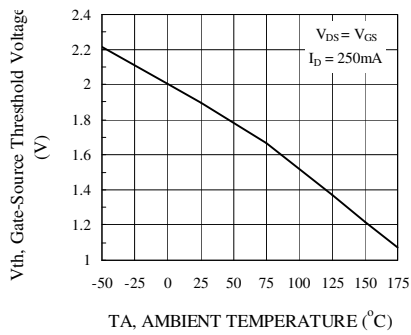


Figure 9. Threshold Vs Ambient Temperature

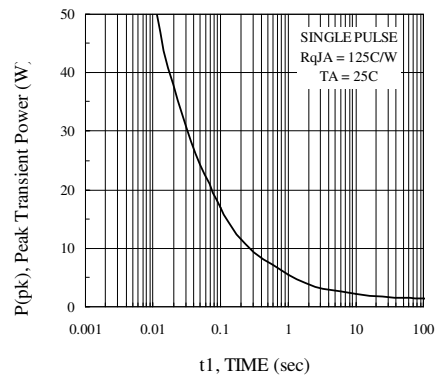


Figure 10. Single Pulse Maximum Power Dissipation

Normalized Thermal Transient Junction to Ambient

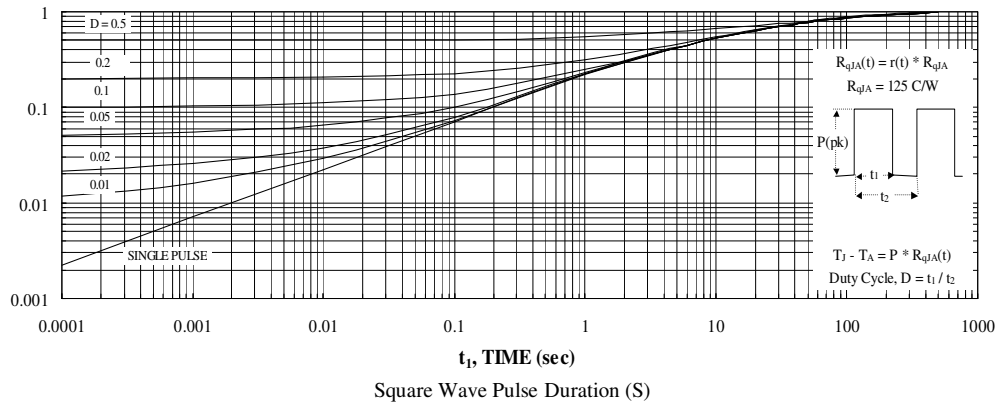
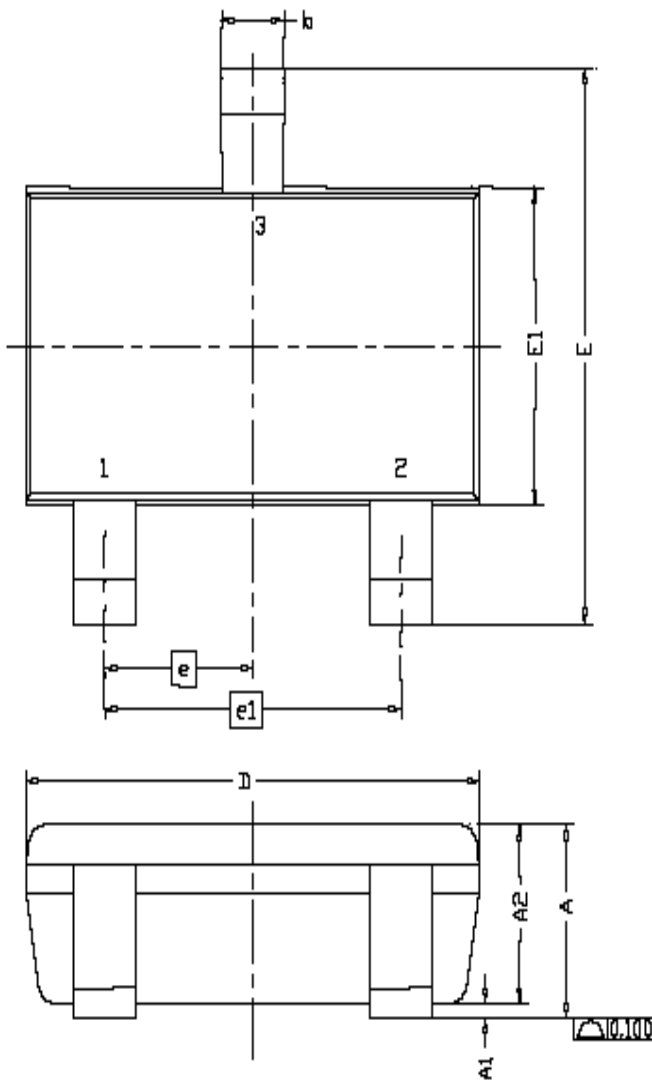


Figure 11. Transient Thermal Response Curve

Package Information



DIM.	MILLIMETERS		
	MIN	NOM	MAX
A	0.935	0.95	1.10
A1	0.01	---	0.10
A2	0.85	0.90	0.925
b	0.30	0.40	0.50
c	0.10	0.15	0.25
D	2.70	2.90	3.10
E	2.60	2.80	3.00
E1	1.40	1.60	1.80
e	0.95 BSC		
e1	1.90 BSC		
L	0.30	0.40	0.60
L1	0.60REF		
L2	0.25BSC		
R	0.10	---	---
θ	0°	4°	8°
θ1	7°NOM		

